



#### **60V N-Channel Enhancement Mode MOSFET**

Voltage

60 V

Current

2.5 A

#### **Features**

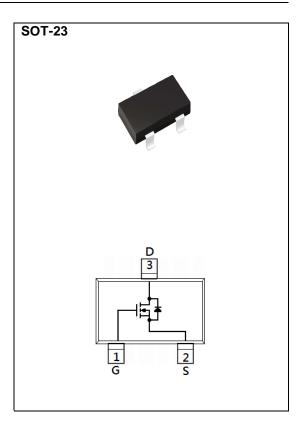
- $R_{DS(ON)}$ ,  $V_{GS}@10V$ ,  $I_D@2A<75m\Omega$
- $R_{DS(ON)}$ ,  $V_{GS}@4.5V$ ,  $I_D@1A<90m\Omega$
- Advanced Trench Process Technology
- Specially Designed for Switch Load, PWM Application, etc
- AEC-Q101 qualified
- Lead free in compliance with EU RoHS 2.0
- Green molding compound as per IEC 61249 standard

#### **Mechanical Data**

• Case: SOT-23 Package

• Terminals : Solderable per MIL-STD-750, Method 2026

• Approx. Weight: 0.0003 ounces, 0.009 grams



### **Maximum Ratings and Thermal Characteristics** (T<sub>A</sub>=25°C unless otherwise noted)

PARAMETER	SYMBOL	LIMIT	UNITS		
Drain-Source Voltage		V <sub>DS</sub>	60	- v	
Gate-Source Voltage		V <sub>GS</sub>	<u>+</u> 20		
Continuous Drain Current (Note 4)		I <sub>D</sub>	2.5	А	
Pulsed Drain Current (Note 1)		I <sub>DM</sub>	10		
Power Dissipation	T <sub>a</sub> =25°C	P <sub>D</sub>	1.25	W	
	Derate above 25°C		10	mW/°C	
Operating Junction and Storage Temperature Range		TJ,TSTG	-55~150	°C	
Typical Thermal Resistance - Junction to Ambient (Note 3,4)		Reja	100	°C/W	





## **Electrical Characteristics** (T<sub>A</sub>=25°C unless otherwise noted)

PARAMETER	SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNITS
Static						
Drain-Source Breakdown Voltage	BV <sub>DSS</sub>	S V <sub>GS</sub> =0V, I <sub>D</sub> =250uA 60	-	-	V	
Gate Threshold Voltage	$V_{GS(th)}$	V <sub>DS</sub> =V <sub>GS</sub> , I <sub>D</sub> =250uA	1	1.75	2.5	V
Drain-Source On-State Resistance	R <sub>DS(on)</sub>	V <sub>GS</sub> =10V, I <sub>D</sub> =2A	-	55	75	mΩ
		V <sub>GS</sub> =4.5V, I <sub>D</sub> =1A	-	63	90	
Zero Gate Voltage Drain Current	IDSS	V <sub>DS</sub> =48V, V <sub>GS</sub> =0V	-	-	1	uA
Gate-Source Leakage Current	Igss	V <sub>GS</sub> = <u>+</u> 20V, V <sub>DS</sub> =0V	-	-	<u>+</u> 100	nA
Dynamic (Note 5)						
Total Gate Charge	$Q_g$	V <sub>DS</sub> =48V, I <sub>D</sub> =2A, V <sub>GS</sub> =10V (Note 1,2)	-	9.3	-	nC
Gate-Source Charge	$Q_{gs}$		-	2.2	-	
Gate-Drain Charge	$Q_gd$		-	1.9	-	
Input Capacitance	Ciss	V <sub>DS</sub> =15V, V <sub>GS</sub> =0V, f=1MHZ	-	509	-	pF
Output Capacitance	Coss		-	47	-	
Reverse Transfer Capacitance	Crss		-	23	-	
Turn-On Delay Time	td <sub>(on)</sub>	$V_{DD}$ =30V, $I_{D}$ =2A, $V_{GS}$ =10V, $R_{G}$ =3.3 $\Omega$ (Note 1,2)	-	3.2	-	ns
Turn-On Rise Time	tr		-	9.7	-	
Turn-Off Delay Time	td <sub>(off)</sub>		-	18.5	-	
Turn-Off Fall Time	tf		-	6.4	-	
Drain-Source Diode						
Maximum Continuous Drain-Source				-	2.5	А
Diode Forward Current	Is					
Diode Forward Voltage	V <sub>SD</sub>	I <sub>S</sub> =1A, V <sub>GS</sub> =0V	-	0.77	1.2	V

#### NOTES:

- 1. Pulse width<a></a>300us, Duty cycle<a></a>2%
- 2. Essentially independent of operating temperature typical characteristics.
- 3. Rejah is the sum of the junction-to-case and case-to-ambient thermal resistance where the case thermal reference is defined as the solder mounting surface of the drain pins mounted on a 1 inch FR-4 with 2oz. square pad of copper.
- 4. The maximum current rating is package limited.
- 5. Guaranteed by design, not subject to production testing.





#### **TYPICAL CHARACTERISTIC CURVES**

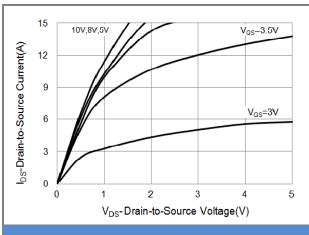
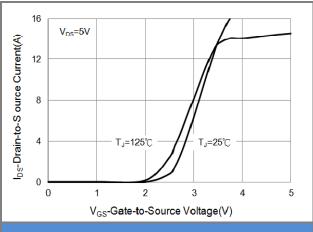


Fig.1 On-Region Characteristics



**Fig.2 Transfer Characteristics** 

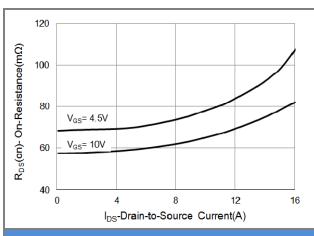


Fig.3 On-Resistance vs. Drain Current

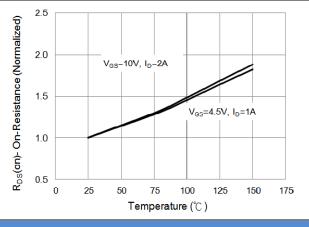


Fig.4 On-Resistance vs. Junction temperature

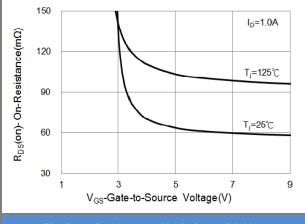
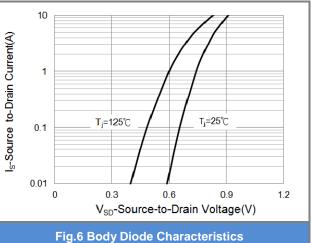


Fig.5 On-Resistance Variation with V<sub>GS</sub>







#### **TYPICAL CHARACTERISTIC CURVES**

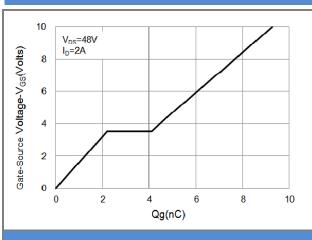


Fig.7 Gate-Charge Characteristics

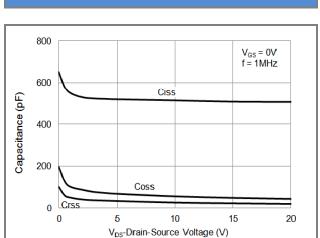


Fig.9 Capacitance vs. Drain-Source Voltage

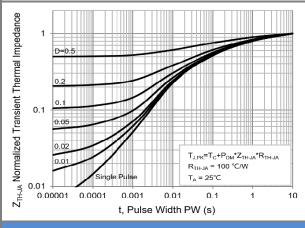


Fig.11 Normalized Transient Thermal Impedance

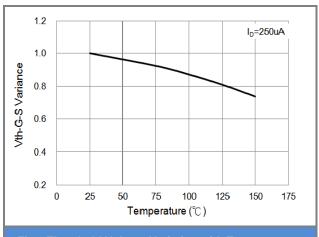


Fig.8 Threshold Voltage Variation with Temperature

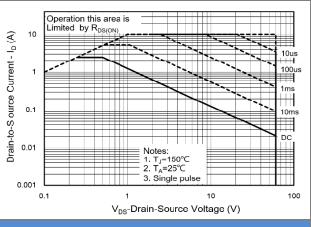


Fig.10 Maximum Safe Operating Area

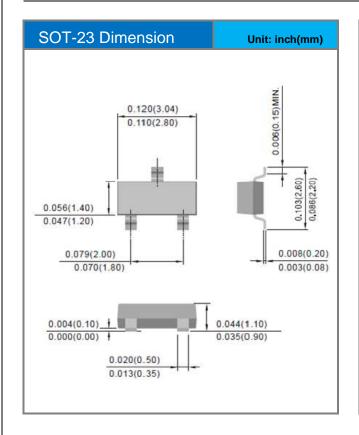


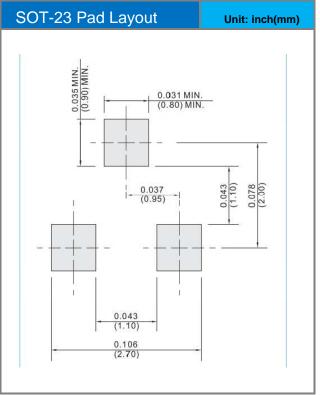


### **Part No Packing Code Version**

Part No Packing Code	Package Type	Packing Type	Marking	Version
PJA3460-AU_R1_000A1	SOT-23	3K pcs / 7" reel	A60	Halogen free

### **Packaging Information & Mounting Pad Layout**









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